

SP7T UltraCMOS™ 2.75 V Switch
100 – 3000 MHz, +68 dBm IIP3

Figure 1. Functional Diagram

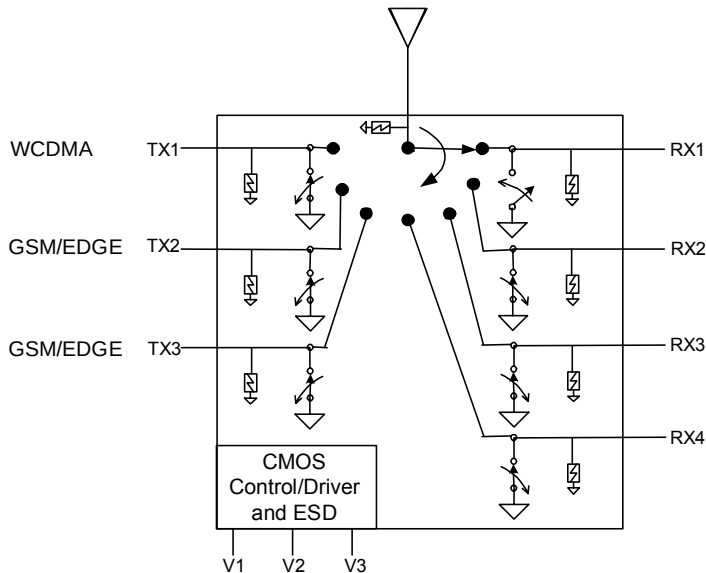
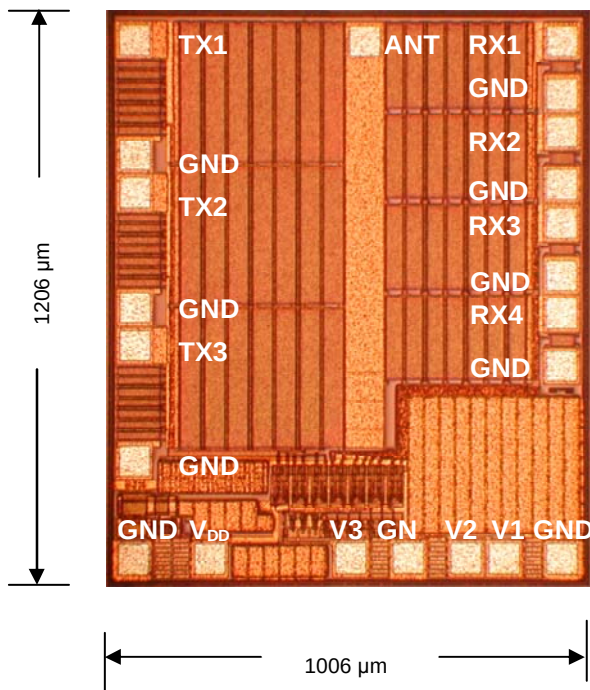


Figure 2. Die Top View*



* Dimensions shown are drawn die size.

Features

- Dedicated TX1 port for WCDMA, TX2 and TX3 ports for GSM/EDGE
- Three pin CMOS logic control with integral decoder/driver
- Exceptional harmonic performance: $2f_0 = -84$ dBc and $3f_0 = -77$ dBc
- Low TX insertion loss: 0.50 dB at 900 MHz, 0.70 dB at 1900 MHz
- TX – RX Isolation of 44 dB at 900 MHz, 38 dB at 1900 MHz
- 1500 V HBM ESD tolerance all ports
- +68 dBm IIP3
- -111 dBm IMD3
- No blocking capacitors required

Product Description

The PE42672 is a HaRP™-enhanced SP7T RF Switch developed on the UltraCMOS™ process technology. It addresses the specific design needs of the Quad-Band GSM Handset Antenna Switch Module Market for use in GSM/EDGE/PCS/DCS/WCDMA handsets. The switch is comprised of three TX ports and four RX ports. TX1 is designed for WCDMA and TX2 and TX3 are designed for GSM/EDGE. The four symmetric RX ports can be used for GSM/EDGE/PCS RX. On-chip CMOS decoder logic facilitates three-pin low voltage CMOS control, while high ESD tolerance of 1500 V at all ports, no blocking capacitor requirements, and on-chip SAW filter over-voltage protection devices make this the ultimate in integration and ruggedness.

Peregrine's HaRP™ technology enhancements deliver high linearity and exceptional harmonics performance. It is an innovative feature of the UltraCMOS™ process, providing performance superior to GaAs with the economy and integration of conventional CMOS.

Table 1. Target Electrical Specifications @ 25 °C, $V_{DD} = 2.75$ V

Parameter	Condition	Typ	Units
Insertion loss ¹	TX - Ant (850 / 900)	0.5	dB
	TX - Ant (1800 / 1900)	0.7	dB
	TX - Ant (2200 UMTS)	0.8	dB
	RX - Ant (850 / 900)	0.8	dB
	RX - Ant (1800 / 1900)	1.0	dB
Return Loss	Port under test in on state	20	dB
Isolation	TX - RX (850 / 900)	44	dB
	TX - RX (1800 / 1900)	38	dB
	TX - TX (850 / 900)	29	dB
	TX - TX (1800 / 1900)	23	dB
	TX1 - RX (1900 / 2200)	37	dB
2nd Harmonic	TX 850 / 900 MHz, +35 dBm output power, 50 Ω	-84	dBc
	TX 1800 / 1900 MHz, +33 dBm output power, 50 Ω	-80	dBc
3rd Harmonic	TX 850 / 900 MHz, +35 dBm output power, 50 Ω	-77	dBc
	TX 1800 / 1900 MHz, +33 dBm output power, 50 Ω	-73	dBc
IMD3 distortion at 2.14 GHz	TX1 Measured at 2.14 GHz at Ant port, input +20 dBm CW signal at 1.95 GHz and -15 dBm CW signal at 1.76 GHz	-111	dBm

Note: 1. Insertion loss specified with optimal impedance matching.

Table 2. Operating Ranges

Parameter	Symbol	Min	Typ	Max	Units
Temperature range	T_{OP}	-40		+85	°C
V_{DD} Supply Voltage	V_{DD}	2.65	2.75	2.85	V
I_{DD} Power Supply Current ($V_{DD} = 2.75$ V)	I_{DD}		13	50	μ A
TX input power ² (VSWR $\leq$ 3:1)	P_{IN}			+35	dBm
RX input power ² (VSWR =1:1)	P_{IN}			+20	dBm
Control Voltage High	V_{IH}	1.4			V
Control Voltage Low	V_{IL}			0.4	V

Note: 2. Assumes RF input period of 4620 μ s and duty cycle of 50%.

Table 3. Absolute Maximum Ratings

Symbol	Parameter/Conditions	Min	Max	Units
V_{DD}	Power supply voltage	-0.3	4.0	V
V_I	Voltage on any input	-0.3	$V_{DD} + 0.3$	V
T_{ST}	Storage temperature range	-65	+150	°C
$P_{IN}(50 \Omega)$	TX input power (50 Ω) ^{3,4}		+38	dBm
	RX input power (50 Ω) ^{3,4}		+23	
$P_{IN}(\infty:1)$	TX input power (VSWR = $\infty:1$) ^{3,4}		+35	dBm
V_{ESD}	ESD Voltage (HBM, MIL_STD 883 Method 3015.7)		1500	V
	ESD Voltage at ANT Port (IEC 61000-4-2)		1700	V

Note: 3. Assumes RF input period of 4620 μ s and duty cycle of 50%.

4. V_{DD} within operating range specified in Table 2.

Part performance is not guaranteed under these conditions. Exposure to absolute maximum conditions for extended periods of time may adversely affect reliability. Stresses in excess of absolute maximum ratings may cause permanent damage.

Table 4. Pin Descriptions

Pin No.	Pin Name	Description
1	ANT	RF Common – Antenna
2 ⁶	TX1	RF I/O – TX1
3 ⁵	GND	Ground (Requires two bond wires)
4 ⁶	TX2	RF I/O – TX2
5 ⁵	GND	Ground
6 ⁵	TX3	RF I/O – TX3
7 ⁵	GND	Ground
8 ⁵	GND	Ground
9	V _{DD}	Supply
10	V3	Switch control input, CMOS logic level
11 ⁵	GND	Ground
12	V2	Switch control input, CMOS logic level
13	V1	Switch control input, CMOS logic level
14 ⁵	GND	Ground
15 ⁵	GND	Ground
16 ⁶	RX4	RF I/O – RX4
17 ⁵	GND	Ground
18 ⁶	RX3	RF I/O – RX3
19 ⁵	GND	Ground
20 ⁶	RX2	RF I/O – RX2
21 ⁵	GND	Ground
22 ⁶	RX1	RF I/O – RX1

Notes: 5. Bond wires should be physically short and connected to ground plane for best performance.

6. Blocking capacitors needed only when non-zero DC voltage present.

Figure 3. Pad Configuration (Top View)

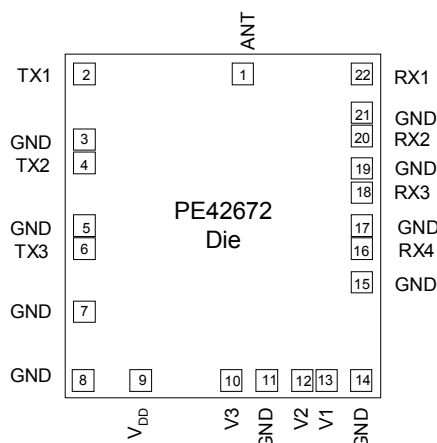


Table 5. Truth Table

Path	V1	V2	V3
RX1 - ANT	0	0	0
RX2 - ANT	1	0	0
RX3 - ANT	0	1	0
RX4 - ANT	1	1	0
TX1 - ANT	0	0	1
TX2 - ANT	1	0	1
TX3 - ANT	0	1	1
All Off	1	1	1

Electrostatic Discharge (ESD) Precautions

When handling this UltraCMOS™ device, observe the same precautions that you would use with other ESD-sensitive devices. Although this device contains circuitry to protect it from damage due to ESD, precautions should be taken to avoid exceeding the specified rating.

Latch-Up Avoidance

Unlike conventional CMOS devices, UltraCMOS™ devices are immune to latch-up.

Table 6. Ordering Information

Order Code	Description	Package	Shipping Method
42672-90	PE42672-DIE-D	Film Frame	Wafer (Gross Die / Wafer Quantity)
42672-99	PE42672-DIE-400G	Waffle Pack	400 Dice / Waffle Pack
42672-00	PE42672-DIE-1H	Evaluation Kit	1/ box

Sales Offices

The Americas

Peregrine Semiconductor Corp.

9450 Carroll Park Drive
San Diego, CA 92121
Tel 858-731-9400
Fax 858-731-9499

Europe

Peregrine Semiconductor Europe

Commercial Products:

Bâtiment Maine
13-15 rue des Quatre Vents
F- 92380 Garches, France
Tel: +33-1-47-41-91-73
Fax : +33-1-47-41-91-73

Space and Defense Products:

180 Rue Jean de Guiramand
13852 Aix-En-Provence cedex 3, France
Tel: +33(0) 4 4239 3361
Fax: +33(0) 4 4239 7227

North Asia Pacific

Peregrine Semiconductor K.K.

5A-5, 5F Imperial Tower
1-1-1 Uchisaiwaicho, Chiyoda-ku
Tokyo 100-0011 Japan
Tel: +81-3-3502-5211
Fax: +81-3-3502-5213

South Asia Pacific

Peregrine Semiconductor

28G, Times Square,
No. 500 Zhangyang Road,
Shanghai, 200122, P.R. China
Tel: +86-21-5836-8276
Fax: +86-21-5836-7652

For a list of representatives in your area, please refer to our Web site at: www.psemi.com

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